ISO742x Low-Power Dual-Channel Digital Isolators

1 Features

- Highest Signaling Rate: 1 Mbps
- Low Power Consumption, Typical I_{CC} per Channel (3.3-V operation):
  - ISO7420: 1.1 mA, ISO7421: 1.5 mA
- Low Propagation Delay – 9 ns Typical
- Low Skew – 300 ps Typical
- Wide T_A Range: –40°C to 125°C (M-Grade)
- 50-kV/μs Transient Immunity, Typical
- Over 25-Year Isolation Integrity at Rated Voltage
- Operates From 3.3-V and 5-V Supply and Logic Levels
- 3.3-V and 5-V Level Translation
- Narrow Body SOIC-8 Package
- Safety and Regulatory Approvals:
  - 4242 V_{PK} Isolation per DIN V VDE V 0884-10 and DIN EN 61010-1
  - 2500 V_{RMS} Isolation for 1 minute per UL 1577
  - CSA Component Acceptance Notice 5A, IEC 60950-1 and IEC 61010-1 Standards
  - CQC Certification per GB4943.1-2011

2 Applications

- Optocoupler Replacement in:
  - Industrial Fieldbus
    - Profibus
    - Modbus
    - DeviceNet™ Data Buses
  - Servo Control Interface
  - Motor Control
  - Power Supplies
  - Battery Packs

3 Description

The ISO7420, ISO7420M and ISO7421 provide galvanic isolation up to 2500 V_{RMS} for 1 minute per UL. These digital isolators have two isolated channels. Each isolation channel has a logic input and output buffer separated by a silicon dioxide (SiO_2) insulation barrier. Used in conjunction with isolated power supplies, these devices prevent noise currents on a data bus or other circuit from entering the local ground and interfering with or damaging sensitive circuitry. The suffix M indicates wide temperature range (–40°C to 125°C).

These devices have TTL input thresholds and require two supply voltages, 3.3 or 5 V, or any combination. All inputs are 5-V tolerant when supplied from a 3.3-V supply.

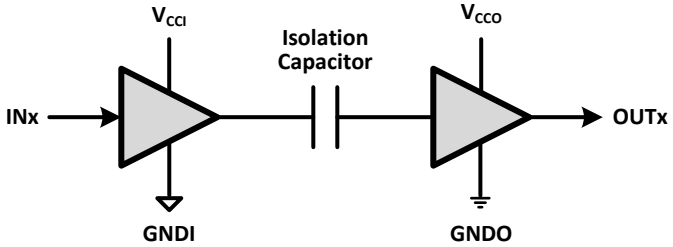
Note: The ISO7420 and ISO7421 are specified for signaling rates up to 1 Mbps. Due to their fast response time, under most cases, these devices will also transmit data with much shorter pulse widths. Designers should add external filtering to remove spurious signals with input pulse duration <20 ns if desired.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ISO7420	SOIC (8)	4.90 mm × 3.91 mm
ISO7420M		
ISO7421		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



V_{CCI} and GNDI are supply and ground connections respectively for the input channels.

V_{CCO} and GNDO are supply and ground connections respectively for the output channels.

An IMPORTANT NOTICE at the end of this data sheet addresses availability, warranty, changes, use in safety-critical applications, intellectual property matters and other important disclaimers. UNLESS OTHERWISE NOTED, this document contains PRODUCTION DATA.

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision H (May 2013) to Revision I — **Page**

- VDE standard changed to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 ... 1
- Added *Pin Configuration and Functions* section, *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 1

Changes from Revision G (May 2013) to Revision H — **Page**

- Changed Feature From: 4~242 Vpeak Isolation To: 4242 Vpeak Isolation ... 1

Changes from Revision F (January 2013) to Revision G — **Page**

- Changed V_{IORM} in the INSULATION CHARACTERISTICS table, Specification value From: 56~6 To: 566 ... 15
- Changed V_{PR} in the Specification value From: 10~62 To: 1062 ... 15
- Changed V_{IOTM} t = 60 s (qualification) Specification value From: 4~242 To: 4242 ... 15

Changes from Revision E (June 2011) to Revision F — **Page**

- Changed Feature From: 242 Vpeak Maximum Isolation-per DIN EN 60747-5-2 (VDE 0884 Part 2) - To: 4~242 Vpeak Isolation ... 1
- Changed Feature From: IEC/VDE and CSA Approvals, IEC 60950-1–IEC 61010-1 End Equipment Standards Approvals, All Approvals Pending To: CSA 60950-1 and IEC 61010-1 Approved ... 1

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- Added table Note to V_{IORM} 15
- Changed V_{IORM} in the INSULATION CHARACTERISTICS table, Specification value From: 56~0 To: 56~6 15
- Changed V_{PR} in the Specification value From: 10~50 To: 10~62 15
- Changed V_{IOTM} t = 60 s (qualification) Specification value From: 4~000 To: 4~242 15
- Changed the IEC 60664-1 RATINGS TABLE. Row - Basic isolation group SPECIFICATION From: III-a To: II 15
- Changed CTI in the PACKAGE CHARACTERISTICS table, Min value From: >175 To 400 15
- Changed the text of NOTE: 16
- Changed the REGULATORY INFORMATION table 17

Changes from Revision D (July 2010) to Revision E **Page**

- Added new fifth bullet to Features and deleted text from 4-kVpeak bullet item 1
- Changed first paragraph in Description from: ISO7420M, ISO7421, and ISO7421M to: ISO7420M and ISO7421 1
- Changed ISO742xM in the ELEC CHAR and SWITCHING CHAR table to ISO7420M 8
- Changed ISO742xM in the ELEC CHAR and SWITCHING CHAR table to ISO7420M 9
- Changed ISO742xM in the ELEC CHAR and SWITCHING CHAR table to ISO7420M 9
- Changed ISO742xM in the ELEC CHAR and SWITCHING CHAR table to ISO7420M 10
- Changed the MAX value in the SWITCHING CHAR table 2nd row from 3.5 to 3.7 and 3rd row from 4 to 4.9 10
- Changed the MAX value in the 2nd SWITCHING CHAR table 2nd row from 4 to 5.6 and 3rd row from 5 to 6.3 10
- Changed the MAX value in the 3rd SWITCHING CHAR table 3rd row from 5 to 8.5 11
- Changed the MAX value in the 4rd SWITCHING CHAR table 3rd row from 6 to 6.8 11
- Changed Regulatory Information table last row, last column from: pending (E181974) to: E181974 17
- Changed Note 2 in Function Table from: ISO7420M, ISO7421, and ISO7421M to: ISO7420M and ISO7421 17

Changes from Revision C (March 2010) to Revision D **Page**

- Updated the Features List 1
- Deleted devices ISO7420F and ISO7420FM from the data sheet 1
- Updated the device Description. Add paragraph - Note: The ISO7420 and ISO7421 1
- Added Tstg to the Absolute Maximum Ratings Table 7
- Updated the *Recommended Operating Conditions* table 7
- Updates throughout the Electrical Characteristics and Switching Characteristics tables 8
- Updated the Supply Current test conditions 8
- Deleted the SUPPLY CURRENT vs SIGNAL RATE (ALL CHANNELS) graphs and the EYE DIAGRAM plots 12
- Changed Figure 7 13
- Changed the V_{IORM}, V_{PR}, and V_{IOTM} unit values From: V To: Vpeak 15
- Changed Minimum internal gap MIN value From: 0.008 To: 0.014mm 15
- Changed the Barrier capacitance, input to output test conditions 15
- Changed the Input capacitance test conditions 15
- Changed V_I From: 5.5 V To: 5.25 V 16
- Changed From: 107mA To: 112mA 16
- Changed V_I From: 3.6 V To: 3.45 V 16
- Changed From: 164mA To: 171mA 16
- Changed Figure 10 16
- Deleted the I_{CC} equations section 16
- Changed the Function Table Output values for PU (Open) From: H/L To: H 17
- Changed Figure 11 17

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Changes from Revision B (February 2010) to Revision C **Page**

- Added devices ISO7420F and ISO7420FM to the data sheet ... 1
- Added The suffix M indicates wide temperature range (–55°C to 125°C) and the suffix F indicates output-low option in fail-safe condition. All other devices without the F suffix default to output-high in fail-safe state. ... 1
- Added ISO7420F and ISO7420FM to the Available Options Table ... 6
- Changed value from a max of 4 mA to a min of –4 mA ... 7
- Changed value from a min of –4 mA to a max of 4 mA ... 7
- Changed Electrical Characteristics Conditions ... 8
- Deleted C_i from the ELECTRICAL CHARACTERISTICS ... 8
- Added (All inputs switching with square wave clock signal for dynamic ICC measurement) ... 8
- Changed ELECTRICAL CHARACTERISTICS conditions ... 9
- Added High-level output voltage ISO7420 / 7421 (3.3-V side) test condition ... 9
- Changed High-level output voltage min value ... 9
- Deleted C_i specification ... 9
- Added (All inputs switching with square wave clock signal for dynamic ICC measurement) ... 9
- Changed ELECTRICAL CHARACTERISTICS conditions ... 9
- Added High-level output voltage ISO7420 / 7421 (5-V side) test condition ... 9
- Changed High-level output voltage min value ... 9
- Deleted C_i specification ... 9
- Added (All inputs switching with square wave clock signal for dynamic ICC measurement) ... 9
- Changed ELECTRICAL CHARACTERISTICS conditions ... 10
- Deleted C_i specification ... 10
- Added (All inputs switching with square wave clock signal for dynamic ICC measurement) ... 10
- Changed SWITCHING CHARACTERISTICS conditions ... 10
- Changed PWD parameter from duration to width ... 10
- Changed *Switching Characteristics* conditions ... 10
- Changed Pulse duration distortion to Pulse width distortion ... 10
- Changed *Switching Characteristics* conditions ... 11
- Changed SWITCHING CHARACTERISTICS conditions ... 11
- Changed Pulse duration distortion to Pulse width distortion ... 11
- Changed SWITCHING CHARACTERISTICS conditions ... 11
- Changed Pulse duration distortion to Pulse width distortion ... 11
- Changed Figure 7 ... 13
- Added input to output and note 1 to Isolation resistance, input to output ... 15
- Changed the Isolation resistance test conditions ... 15
- Changed the Isolation resistance test conditions ... 15
- Added note 1 to Barrier capacitance, input to output ... 15
- Added Input capacitance ... 15
- Changed T_J = 170°C to T_J = 150°C ... 16
- Changed From: 124mA To: 107mA ... 16
- Changed T_J = 170°C to T_J = 150°C ... 16
- Changed From: 190mA To: 164mA ... 16
- Changed Figure 10 ... 16
- Changed the Function Table Output values for PU (Open) From: H To: H/L ... 17
- Changed the Function Table Output values for PU (X) From: H To: H/L ... 17
- Changed the Function Table Output values for PU (X) From: H/L To: H ... 17

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- Added Note (2) in the Function Table 17
- Changed Figure 11 17

Changes from Revision A (December 2009) to Revision B **Page**

- Switching Characteristics Table, Added Note (2) - Typical specifications are measured at ideal conditions of 25°C. Max or Min specifications are measured at worst case conditions for V_{CC} and temperature. 8

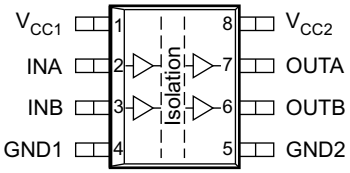
Changes from Original (June 2009) to Revision A **Page**

- Added devices ISO7420 and ISO7420M to the data sheet 1
- Added the I_{CC} equations section 16

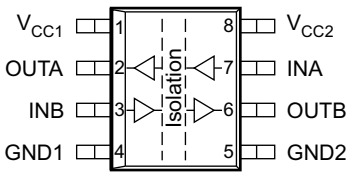
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5 Pin Configuration and Functions

ISO7420: D Package
8-Pin SOIC
(Top View)



ISO7421: D Package
8-Pin SOIC
(Top View)



Pin Functions

PIN			I/O	DESCRIPTION
NAME	ISO7420	ISO7421		
GND1	4	4	—	Ground connection for V_{CC1}
GND2	5	5	—	Ground connection for V_{CC2}
INA	2	7	I	Input, channel A
INB	3	3	I	Input, channel B
OUTA	7	2	O	Output, channel A
OUTB	6	6	O	Output, channel B
V_{CC1}	1	1	—	Power supply, V_{CC1}
V_{CC2}	8	8	—	Power supply, V_{CC2}

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6 Specifications

6.1 Absolute Maximum Ratings

See (1)		MIN	MAX	UNIT
V_{CC}	Supply voltage(2), V_{CC1}, V_{CC2}	–0.5	6	V
V_I	Voltage at IN, OUT	–0.5	V_{CC} + 0.5(3)	V
I_O	Output current	–15	15	mA
$T_{J(max)}$	Maximum junction temperature		150	°C
T_{stg}	Storage temperature	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values.
(3) Maximum voltage must not exceed 6 V.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Field-induced charged-device model, JEDEC Standard 22, Test Method C101	±1500	
		Machine model, ANSI/ESDS5.2-1996	±200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V_{CC1}, V_{CC2}	Supply voltage - 3.3-V operation		3.15	3.3	3.45	V
	Supply voltage - 5-V operation		4.75	5	5.25	
I_{OH}	High-level output current		–4			mA
I_{OL}	Low-level output current				4	mA
V_{IH}	High-level input voltage		2		5.25	V
V_{IL}	Low-level input voltage		0		0.8	V
$1/t_{ui}$	Signaling rate		0		1	Mbps
t_{ui}	Input pulse duration		1			us
T_J(1)	Junction temperature		–40		136	°C
T_A	Ambient temperature	ISO7420, ISO7421	-40	25	105	°C
		ISO7420M	-40	25	125	

(1) To maintain the recommended operating conditions for T_J, see the *Thermal Information*.

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6.4 Thermal Information

THERMAL METRIC[1]			ISO742x D (SOIC) 8 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	Low-K Board	212	°C/W
		High-K Board	116.6	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance		71.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance		57.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter		28.3	°C/W
ψ_{JB}	Junction-to-board characterization parameter		56.8	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

6.5 Electrical Characteristics: V_{CC1} and V_{CC2} at 5 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –4 mA; see Figure 6.		V_{CCO}[1] – 0.8	4.6		V
		I_{OH} = –20 µA; see Figure 6.		V_{CCO} – 0.1	5		
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; see Figure 6.			0.2	0.4	V
		I_{OL} = 20 µA; see Figure 6.			0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				400		mV
I_{IH}	High-level input current	INx at 0 V or V_{CCI} [1]				10	µA
I_{IL}	Low-level input current			–10			µA
CMTI	Common-mode transient immunity	V_I = V_{CCI} or 0 V; see Figure 8.		25	50		kV/µs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC ICC MEASUREMENT)							
ISO7420							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		0.4	1	mA
I_{CC2}	Supply current for V_{CC2}				3	6	
ISO7421							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		2	4	mA
I_{CC2}	Supply current for V_{CC2}				2	4	

(1) V_{CCI} = Input-side power supply, V_{CCO} = Output-side power supply

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6.6 Electrical Characteristics: V_{CC1} at 5 V ±5%, V_{CC2} at 3.3 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –4 mA; see Figure 6.	ISO7421 (5-V side)	V_{CCO} (1) – 0.8	4.6		V
			ISO7420 / 7421 (3.3-V side).	V_{CCO} – 0.4	3		
		I_{OH} = –20 µA; see Figure 6,		V_{CCO} – 0.1	V_{CC}		
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; see Figure 6.			0.2	0.4	V
		I_{OL} = 20 µA; see Figure 6.			0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				400		mV
I_{IH}	High-level input current	INx at 0 V or V_{CCI} (1)				10	µA
I_{IL}	Low-level input current			–10			µA
CMTI	Common-mode transient immunity	V_I = V_{CCI} or 0 V; seeFigure 8 .		25	40		kV/µs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC ICC MEASUREMENT)							
ISO7420							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		0.4	1	mA
I_{CC2}	Supply current for V_{CC2}				2	4.5	mA
ISO7421							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		2	4	mA
I_{CC2}	Supply current for V_{CC2}				1.5	3.5	mA

(1) V_{CCI} = Input-side power supply, V_{CCO} = Output-side power supply

6.7 Electrical Characteristics: V_{CC1} at 3.3 V ±5%, V_{CC2} at 5 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –4 mA; see Figure 6.	ISO7420 / 7421 (5-V side).	V_{CCO} (1) – 0.8	4.6		V
			ISO7421 (3.3-V side)	V_{CCO} – 0.4	3		
		I_{OH} = –20 µA; see Figure 6		V_{CCO} – 0.1	V_{CC}		
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; see Figure 6.			0.2	0.4	V
		I_{OL} = 20 µA; see Figure 6.			0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				400		mV
I_{IH}	High-level input current	INx at 0 V or V_{CCI} (1)				10	µA
I_{IL}	Low-level input current			–10			µA
CMTI	Common-mode transient immunity	V_I = V_{CCI} or 0 V; see Figure 8.		25	40		kV/µs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC ICC MEASUREMENT)							
ISO7420							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		0.2	0.7	mA
I_{CC2}	Supply current for V_{CC2}				3	6	
ISO7421							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		1.5	3.5	mA
I_{CC2}	Supply current for V_{CC2}				2	4	

(1) V_{CCI} = Input-side power supply, V_{CCO} = Output-side power supply

6.8 Electrical Characteristics: V_{CC1} and V_{CC2} at 3.3 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –4 mA; see Figure 6.		V_{CCO} (1) – 0.4	3		V
		I_{OH} = –20 µA; see Figure 6.		V_{CCO} – 0.1	3.3		
V_{OL}	Low-level output voltage	I_{OL} = 4 mA; see Figure 6.			0.2	0.4	V
		I_{OL} = 20 µA; see Figure 6.			0	0.1	
$V_{I(HYS)}$	Input threshold voltage hysteresis				400		mV
I_{IH}	High-level input current	INx at 0 V or V_{CCI} (1)				10	µA
I_{IL}	Low-level input current			–10			µA
CMTI	Common-mode transient immunity	V_I = V_{CCI} or 0 V; seeFigure 8 .		25	40		kV/µs
SUPPLY CURRENT (ALL INPUTS SWITCHING WITH SQUARE WAVE CLOCK SIGNAL FOR DYNAMIC ICC MEASUREMENT)							
ISO7420							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		0.2	0.7	mA
I_{CC2}	Supply current for V_{CC2}				2	4.5	
ISO7421							
I_{CC1}	Supply current for V_{CC1}	DC to 1 Mbps	V_I = V_{CCI} or 0 V, 15 pF load		1.5	3.5	mA
I_{CC2}	Supply current for V_{CC2}				1.5	3.5	

(1) V_{CCI} = Input-side power supply, V_{CCO} = Output-side power supply

6.9 Power Dissipation Characteristics

THERMAL METRIC			ISO742x D (SOIC) 8 PINS	UNIT
P_D	Device power dissipation	V_{CC1} = V_{CC2} = 5.25 V, T_J = 150°C, C_L = 15 pF Input a 1-Mbps 50% duty-cycle square wave	55	mW

6.10 Switching Characteristics: V_{CC1} and V_{CC2} at 5 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See Figure 6.		9	14	ns
PWD (1)	Pulse width distortion $\|t_{PHL} - t_{PLH}\|$			0.3	3.7	ns
$t_{sk(pp)}$	Part-to-part skew time				4.9	ns
$t_{sk(o)}$	Channel-to-channel output skew time				3.6	ns
t_r	Output signal rise time	See Figure 6.		1		ns
t_f	Output signal fall time			1		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 7.		6		µs

(1) Also known as pulse skew.

6.11 Switching Characteristics: V_{CC1} at 5 V ±5%, V_{CC2} at 3.3 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See Figure 6.		10	17	ns
PWD (1)	Pulse width distortion $\|t_{PHL} - t_{PLH}\|$			0.5	5.6	ns
$t_{sk(pp)}$	Part-to-part skew time				6.3	ns
$t_{sk(o)}$	Channel-to-channel output skew time				4	ns
t_r	Output signal rise time	See Figure 6.		2		ns

(1) Also known as pulse skew.

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Switching Characteristics: V_{CC1} at 5 V ±5%, V_{CC2} at 3.3 V ±5% (continued)

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_f	Output signal fall time			2		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 7.		6		µs

6.12 Switching Characteristics: V_{CC1} at 3.3 V ±5%, V_{CC2} at 5 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See Figure 6.		10	17	ns
PWD (1)	Pulse width distortion $\|t_{PHL} - t_{PLH}\|$			0.5	4	ns
$t_{sk(pp)}$	Part-to-part skew time				8.5	ns
$t_{sk(o)}$	Channel-to-channel output skew time				4	ns
t_r	Output signal rise time	See Figure 6.		2		ns
t_f	Output signal fall time			2		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 7.		6		µs

(1) Also known as pulse skew.

6.13 Switching Characteristics: V_{CC1} and V_{CC2} at 3.3 V ±5%

T_A = –40°C to 125°C for ISO7420M, T_A = –40°C to 105°C for ISO742x

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}, t_{PHL}	Propagation delay time	See Figure 6.		12	20	ns
PWD (1)	Pulse width distortion $\|t_{PHL} - t_{PLH}\|$			1	5	ns
$t_{sk(pp)}$	Part-to-part skew time				6.8	ns
$t_{sk(o)}$	Channel-to-channel output skew time				5.5	ns
t_r	Output signal rise time	See Figure 6.		2		ns
t_f	Output signal fall time			2		ns
t_{fs}	Fail-safe output delay time from input power loss	See Figure 7.		6		µs

(1) Also known as pulse skew.

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6.14 Typical Characteristics

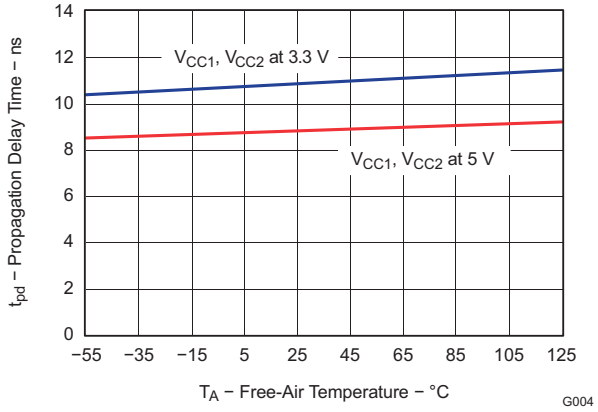


Figure 1. Propagation Delay Time vs Free-Air Temperature

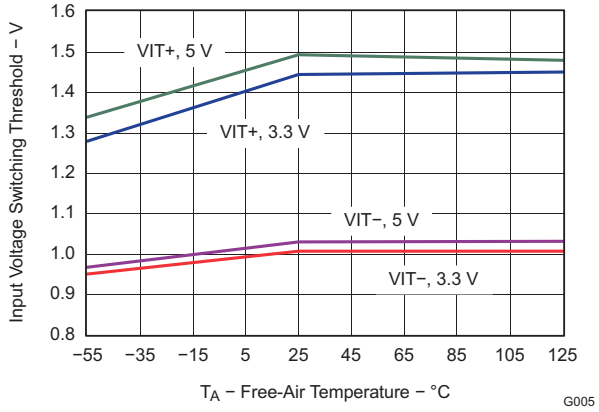


Figure 2. Input Voltage Switching Threshold vs Free-Air Temperature

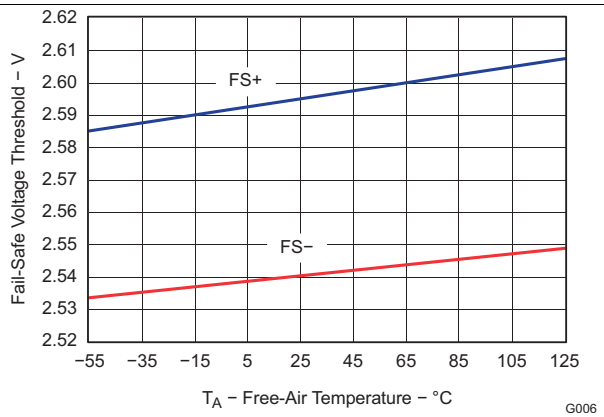


Figure 3. Fail-Safe Voltage Threshold vs Free-Air Temperature

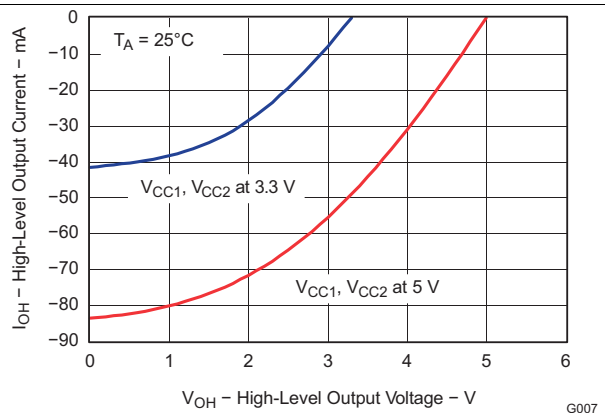


Figure 4. High-Level Output Current vs High-Level Output Voltage

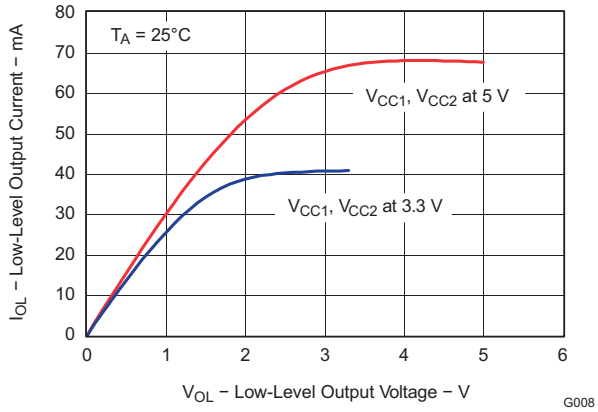
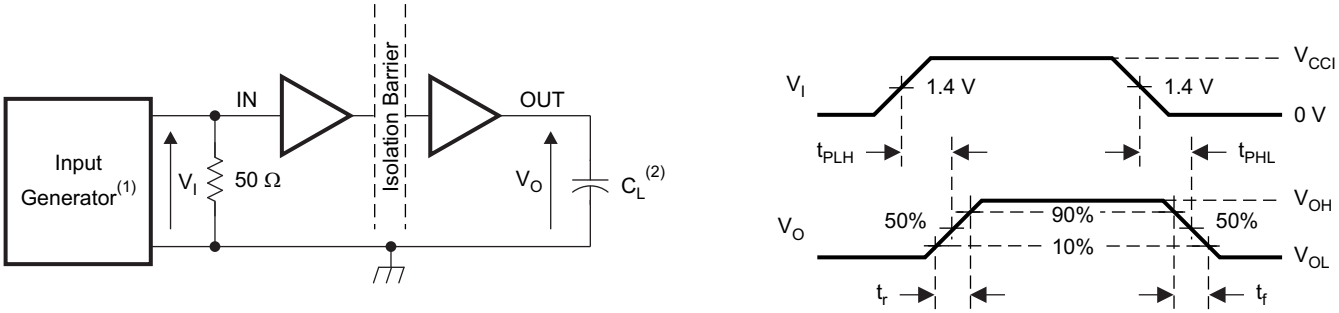


Figure 5. Low-Level Output Current vs Low-Level Output Voltage

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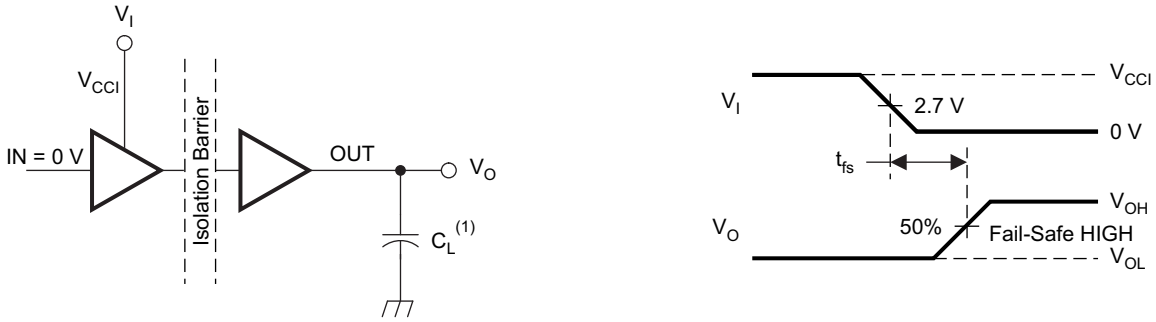
7 Parameter Measurement Information



(1) The input pulse is supplied by a generator having the following characteristics: PRR ≤ 50 kHz, 50% duty cycle, t_r ≤ 3 ns, t_f ≤ 3 ns, Z_O = 50 Ω. At the input, a 50-Ω resistor is required to terminate the Input Generator signal. It is not needed in actual application.

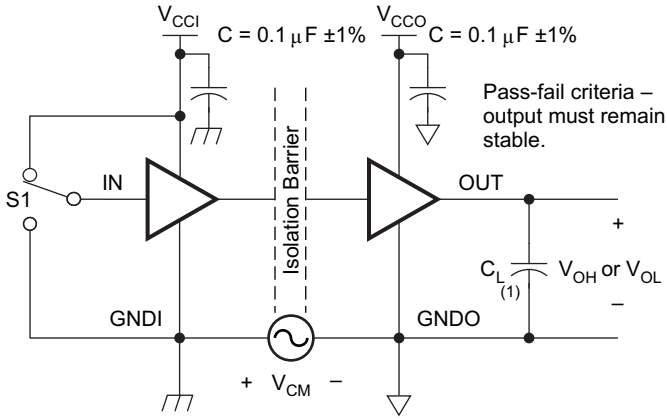
(2) C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 6. Switching Characteristic Test Circuit and Voltage Waveforms



(1) C_L = 15 pF ± 20% includes instrumentation and fixture capacitance.

Figure 7. Fail-Safe Output Delay-Time Test Circuit and Voltage Waveforms



(1) C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.

Figure 8. Common-Mode Transient Immunity Test Circuit

8 Detailed Description

8.1 Overview

The isolator in Figure 9 is based on a capacitive isolation barrier technique. The I/O channel of the device consists of two internal data channels, a high-frequency channel (HF) with a bandwidth from 100 kbps up to 1 Mbps, and a low-frequency channel (LF) covering the range from 100 kbps down to DC. In principle, a single- ended input signal entering the HF-channel is split into a differential signal via the inverter gate at the input. The following capacitor-resistor networks differentiate the signal into transients, which then are converted into differential pulses by two comparators. The comparator outputs drive a NOR-gate flip-flop whose output feeds an output multiplexer. A decision logic (DCL) at the driving output of the flip-flop measures the durations between signal transients. If the duration between two consecutive transients exceeds a certain time limit, (as in the case of a low-frequency signal), the DCL forces the output-multiplexer to switch from the high- to the low-frequency channel.

Because low-frequency input signals require the internal capacitors to assume prohibitively large values, these signals are pulse-width modulated (PWM) with the carrier frequency of an internal oscillator, thus creating a sufficiently high frequency signal, capable of passing the capacitive barrier. As the input is modulated, a low-pass filter (LPF) is needed to remove the high-frequency carrier from the actual data before passing it on to the output multiplexer.

8.2 Functional Block Diagram

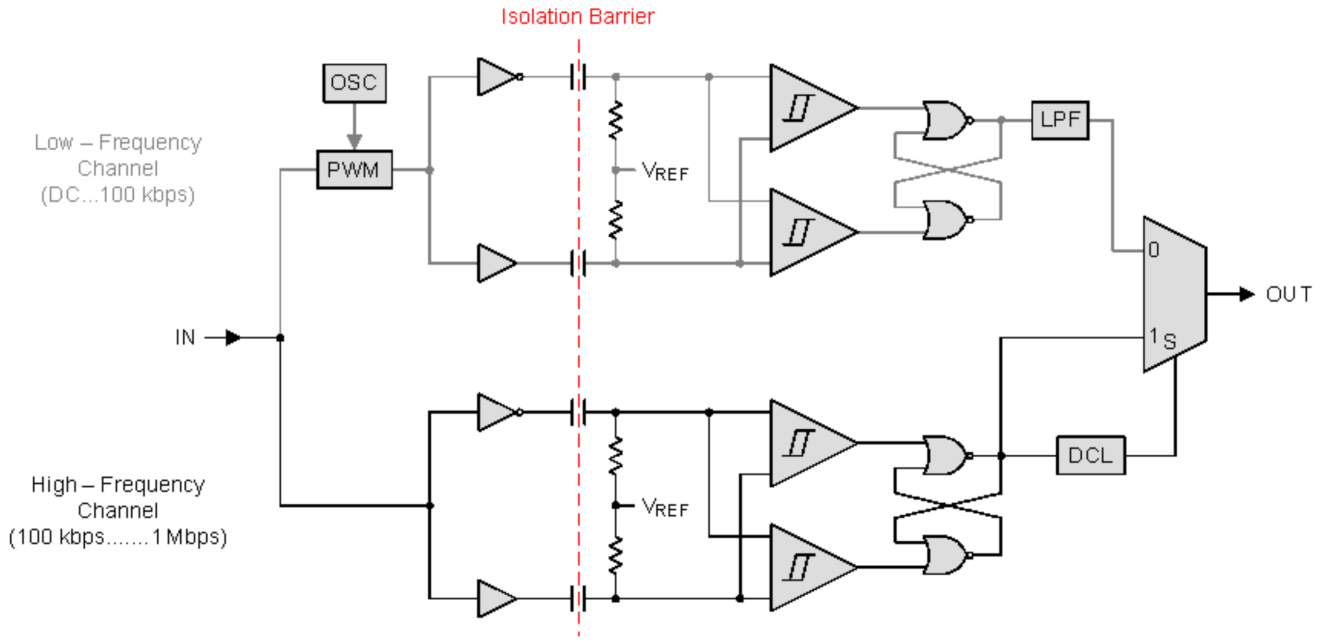


Figure 9. Conceptual Block Diagram of a Digital Capacitive Isolator

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8.3 Feature Description

8.3.1 Insulation Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER[1]		TEST CONDITIONS	SPECIFICATION	UNIT
DIN V VDE V 0884-10 (VDE V 0884-10):2006-12				
V_{IORM}	Maximum working insulation voltage		566	V_{PK}
V_{PR}	Input-to-output test voltage	t = 1 s (100% production), partial discharge 5 pC	1062	V_{PK}
V_{IOTM}	Transient overvoltage	t = 60 s (qualification)	4242	V_{PK}
		t = 1 s (100% production)		
R_S	Insulation resistance	V_{IO} = 500 V at T_S	$>10^9$	Ω
	Pollution degree		2	
UL 1577				
V_{ISO}	Isolation voltage per UL	$V_{TEST} = V_{ISO}$ = 2500 V_{RMS}, t = 60 s (qualification) V_{TEST} = 1.2 x V_{ISO} = 3000 V_{RMS}, t = 1 s (100% production)	2500	V_{RMS}

(1) Climatic Classification 40/125/21

Table 1. IEC 60664-1 Ratings Table

PARAMETER	TEST CONDITIONS	SPECIFICATION
Material group		II
Installation classification	Rated mains voltage ≤ 150 V_{RMS}	I–IV
	Rated mains voltage ≤ 300 V_{RMS}	I–III

8.3.2 Package Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	4			mm
L(I02)	Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	4			mm
CTI	Tracking resistance (comparative tracking index)	DIN EN 60112 (VDE 0303-11); IEC 60112	>400			V
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	0.014			mm
R_{IO}	Isolation resistance, input to output[1]	V_{IO} = 500 V, T_A = 25°C		$>10^{12}$		Ω
		V_{IO} = 500 V, 100°C ≤ T_A ≤ max		$>10^{11}$		Ω
C_{IO}	Barrier capacitance, input to output[1]	V_{IO} = 0.4 sin (2πft), f = 1 MHz		1		pF
C_I	Input capacitance[2]	$V_I = V_{CC}/2$ + 0.4 sin (2πft), f = 1 MHz, V_{CC} = 5 V		1		pF

(1) All pins on each side of the barrier tied together creating a two-terminal device.
(2) Measured from input pin to ground.

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NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal in certain cases. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

8.3.3 Safety Limiting Values

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S	Safety input, output, or supply current	θ_{JA} = 212°C/W, V_I = 5.25 V, T_J = 150°C, T_A = 25°C			112	mA
		θ_{JA} = 212°C/W, V_I = 3.45 V, T_J = 150°C, T_A = 25°C			171	
T_S	Maximum safety temperature				150	°C

The safety-limiting constraint is the absolute-maximum junction temperature specified in the *Absolute Maximum Ratings* table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the *Thermal Information* table is that of a device installed in the JESD51-3, Low-Effective-Thermal-Conductivity Test Board for Leaded Surface-Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

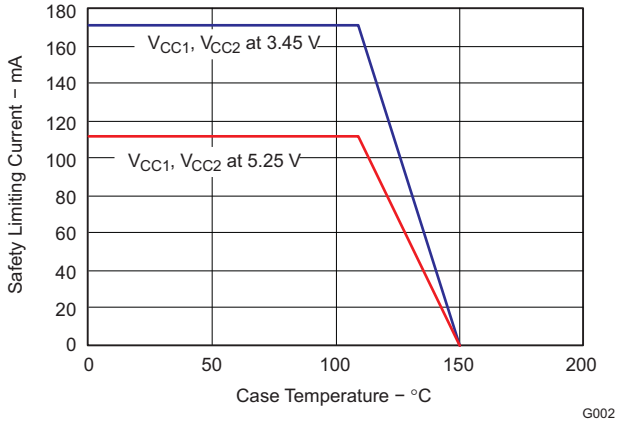


Figure 10. θ_{JC} Thermal Derating Curve per VDE

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8.3.4 Regulatory Information

VDE	CSA	UL	CQC
Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 and DIN EN 61010-1 (VDE 0411-1): 2011-07	Approved under CSA Component Acceptance Notice #5A	Recognized under UL1577 Component Recognition Program(1)	Certified according to GB4943.1-2011
Basic Insulation Maximum Transient Overvoltage, 4242 V_{PK} Maximum Working Voltage, 566 V_{PK}	Basic insulation per CSA 60950-1-07 and IEC 60950-1 (2nd Ed), 390 VRMS maximum working voltage	Single Protection, 2500 V_{RMS}	Basic Insulation, Altitude ≤ 5000 m, Tropical Climate, 250 V_{RMS} maximum working voltage
Certificate number: 40016131	Master contract number: 220991	File number: E181974	Certificate number: CQC14001109540

(1) Production tested ≥ 3000 V_{RMS} for 1 second in accordance with UL 1577.

8.4 Device Functional Modes

Table 2. Function Table(1)

VCCI	VCCO	INPUT INA, INB	OUTPUT OUTA, OUTB
PU	PU	H	H
		L	L
		Open	H(2)
PD	PU	X	H(2)
X	PD	X	Undetermined

(1) V_{CCI} = Input-side power supply; V_{CCO} = Output-side power supply; PU = Powered up (V_{CC} ≥ 3.15 V); PD = Powered down (V_{CC} ≤ 2.1 V); X = Irrelevant; H = High level; L = Low level
(2) In fail-safe condition, output defaults to high level.

8.4.1 Device I/O Schematics

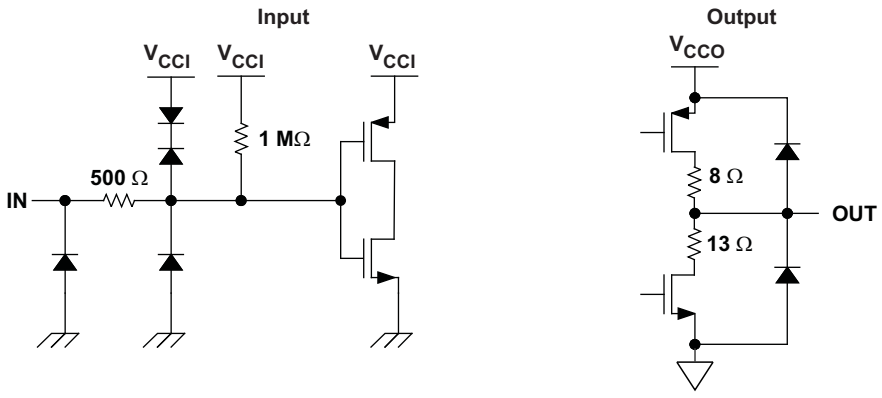


Figure 11. Device I/O Schematics

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

ISO742x utilize single-ended TTL-logic switching technology. Its supply voltage range is from 3.15 V to 5.25 V for both supplies, V_{CC1} and V_{CC2}. When designing with digital isolators, it is important to keep in mind that due to the single-ended design structure, digital isolators do not conform to any specific interface standard and are only intended for isolating single-ended CMOS or TTL digital signal lines. The isolator is typically placed between the data controller (i.e. µC or UART), and a data converter or a line transceiver, regardless of the interface type or standard.

9.2 Typical Application

ISO7421 can be used with Texas Instruments' mixed signal micro-controller, digital-to-analog converter, transformer driver, and voltage regulator to create an isolated 4-20 mA current loop.

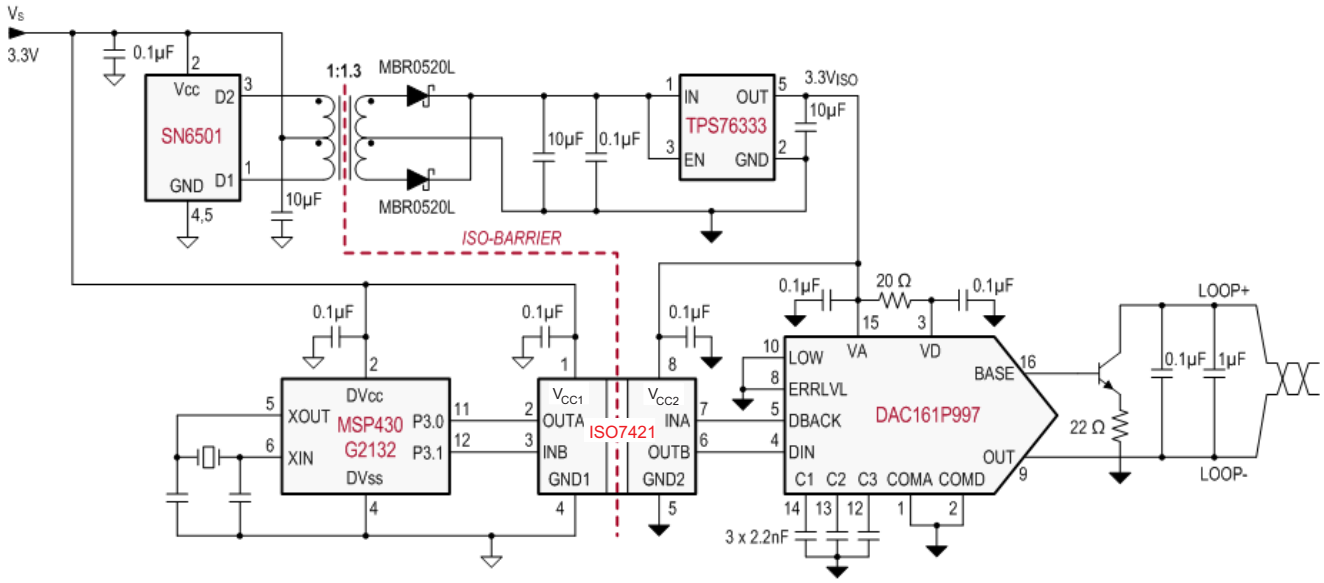


Figure 12. Isolated 4-20 mA Current Loop

9.2.1 Design Requirements

Unlike optocouplers, which require external components to improve performance, provide bias, or limit current, the ISO742x only require two external bypass capacitors to operate.

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Typical Application (continued)

9.2.2 Detailed Design Procedure

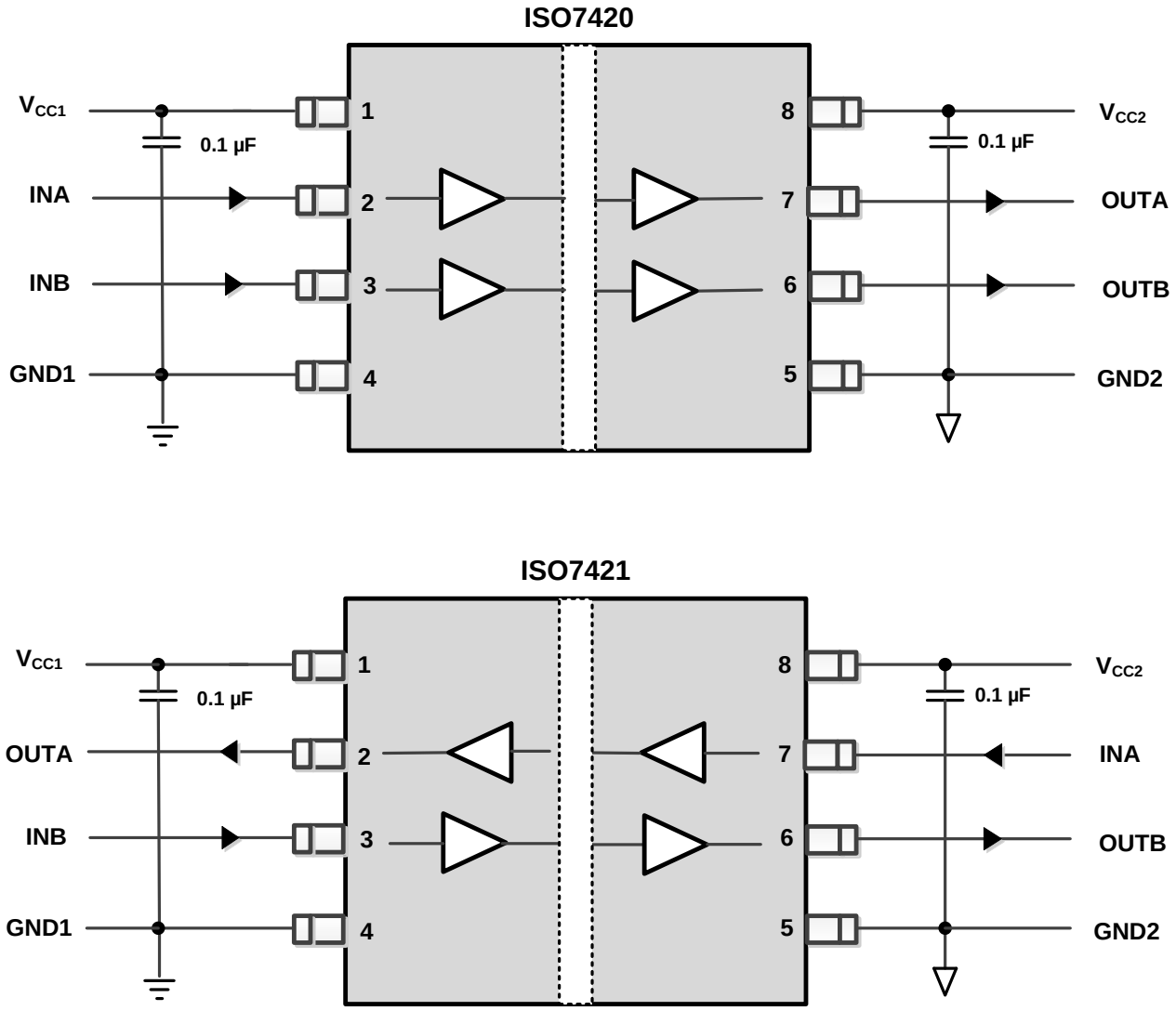


Figure 13. Typical ISO7420 and ISO7421 Circuit Hookup

9.2.3 Application Curve

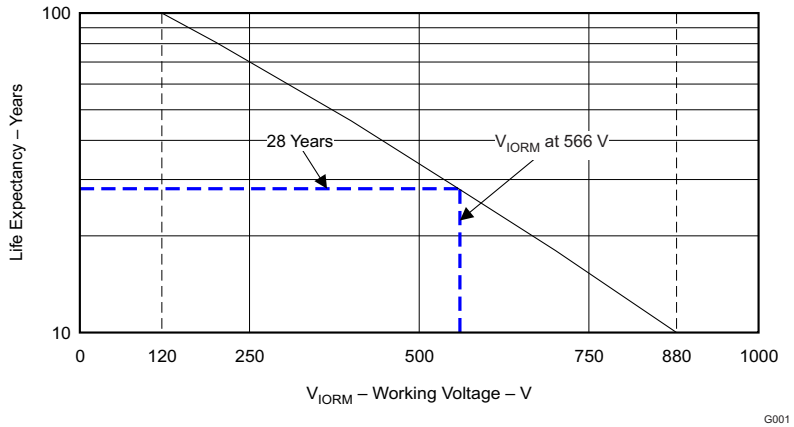


Figure 14. Life Expectancy vs Working Voltage

10 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, a 0.1 µF bypass capacitor is recommended at input and output supply pins (V_{CC1} and V_{CC2}). The capacitors should be placed as close to the supply pins as possible. If only a single primary-side power supply is available in an application, isolated power can be generated for the secondary-side with the help of a transformer driver such as Texas Instruments' SN6501. For such applications, detailed power supply design and transformer selection recommendations are available in SN6501 datasheet (SLLSEA0).

11 Layout

11.1 Layout Guidelines

A minimum of four layers is required to accomplish a low EMI PCB design (see Figure 15). Layer stacking should be in the following order (top-to-bottom): high-speed signal layer, ground plane, power plane and low-frequency signal layer.

- Routing the high-speed traces on the top layer avoids the use of vias (and the introduction of their inductances) and allows for clean interconnects between the isolator and the transmitter and receiver circuits of the data link.
- Placing a solid ground plane next to the high-speed signal layer establishes controlled impedance for transmission line interconnects and provides an excellent low-inductance path for the return current flow.
- Placing the power plane next to the ground plane creates additional high-frequency bypass capacitance of approximately 100pF/in^2.
- Routing the slower speed control signals on the bottom layer allows for greater flexibility as these signal links usually have margin to tolerate discontinuities such as vias.

If an additional supply voltage plane or signal layer is needed, add a second power / ground plane system to the stack to keep it symmetrical. This makes the stack mechanically stable and prevents it from warping. Also the power and ground plane of each power system can be placed closer together, thus increasing the high-frequency bypass capacitance significantly.

For detailed layout recommendations, see Application Note *Digital Isolator Design Guide*, SLLA284.

11.1.1 PCB Material

For digital circuit boards operating below 150 Mbps, (or rise and fall times higher than 1 ns), and trace lengths of up to 10 inches, use standard FR-4 epoxy-glass as PCB material. FR-4 (Flame Retardant 4) meets the requirements of Underwriters Laboratories UL94-V0, and is preferred over cheaper alternatives due to its lower dielectric losses at high frequencies, less moisture absorption, greater strength and stiffness, and its self-extinguishing flammability-characteristics.

11.2 Layout Example

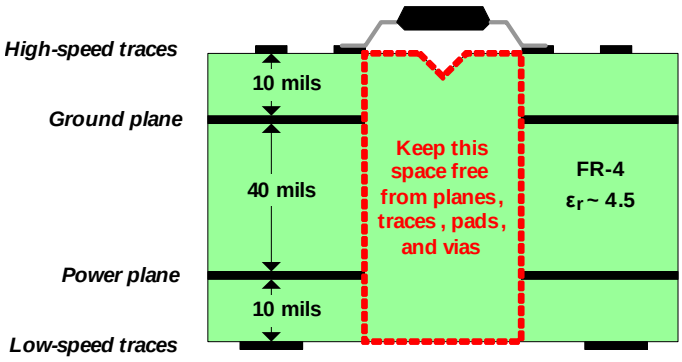


Figure 15. Recommended Layer Stack

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12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- *SN6501 Transformer Driver for Isolated Power Supplies*, SLLSEA0
- *Isolation Glossary*, SLLA353
- *Digital Isolator Design Guide*, SLLA284

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 3. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
ISO7420	Click here	Click here	Click here	Click here	Click here
ISO7420M	Click here	Click here	Click here	Click here	Click here
ISO7421	Click here	Click here	Click here	Click here	Click here
ISO7421M	Click here	Click here	Click here	Click here	Click here

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

DeviceNet, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7420D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	IS7420	Samples
ISO7420DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	IS7420	Samples
ISO7420MD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420M	Samples
ISO7420MDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	I7420M	Samples
ISO7421D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	IS7421	Samples
ISO7421DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	IS7421	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

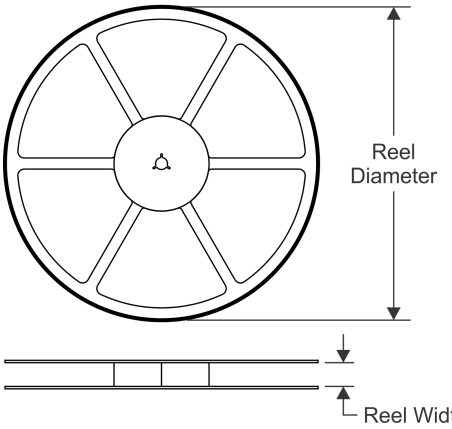
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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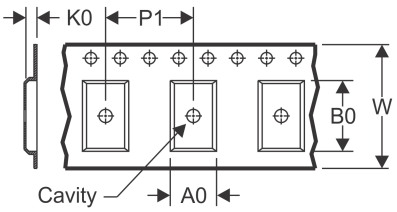
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TAPE AND REEL INFORMATION

REEL DIMENSIONS

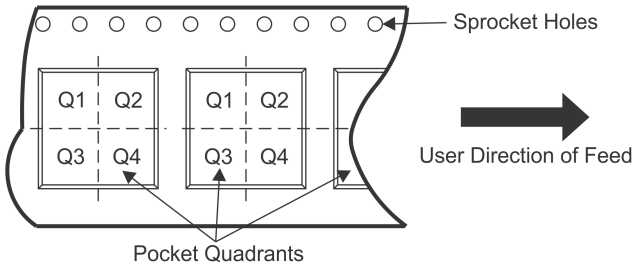


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

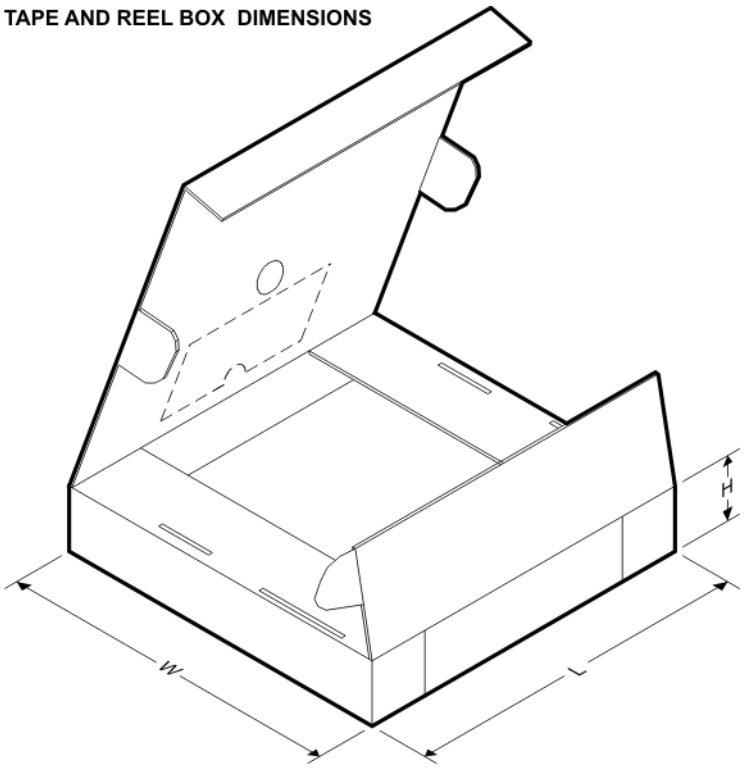
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7420DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7420MDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
ISO7421DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

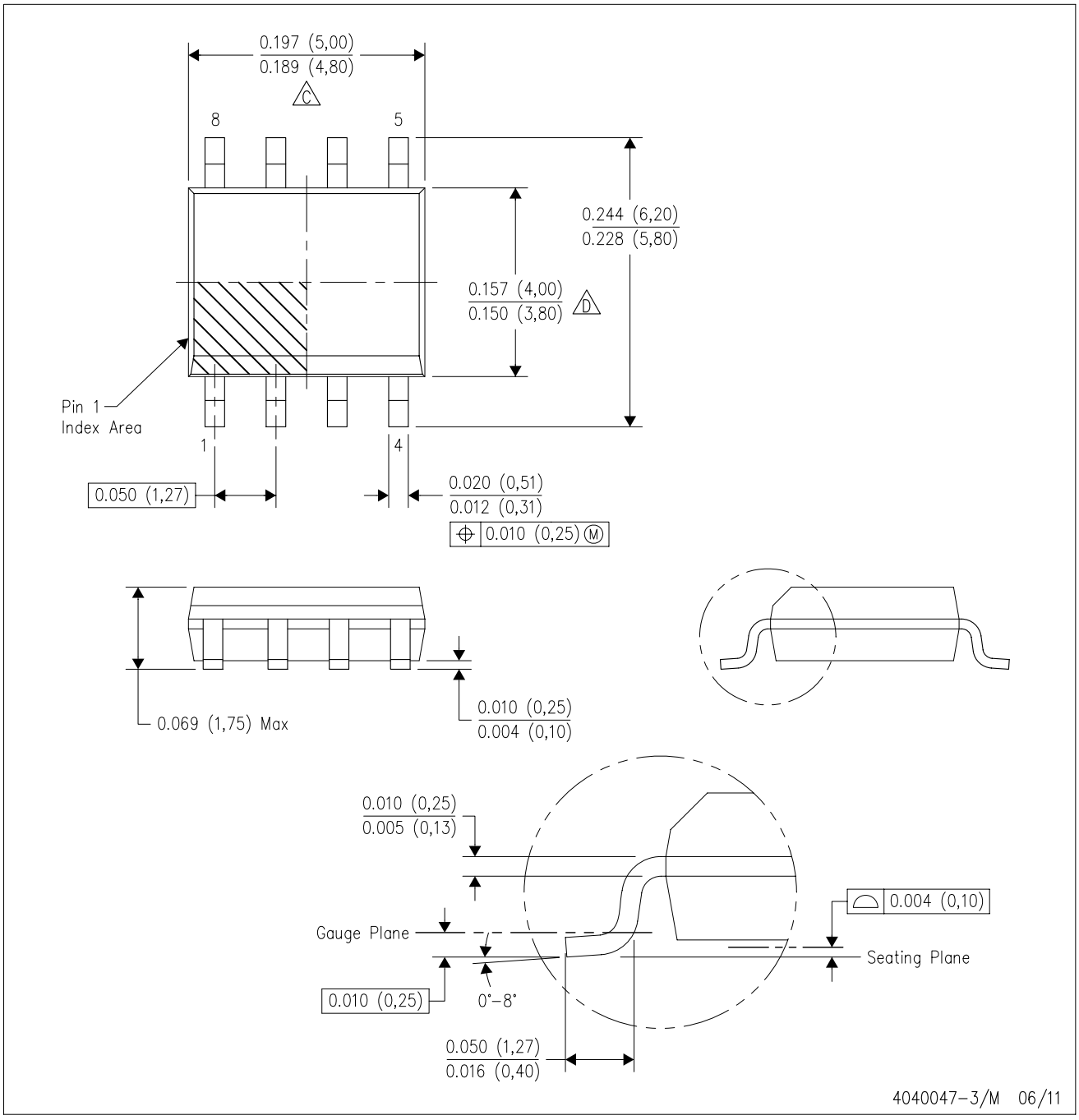
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

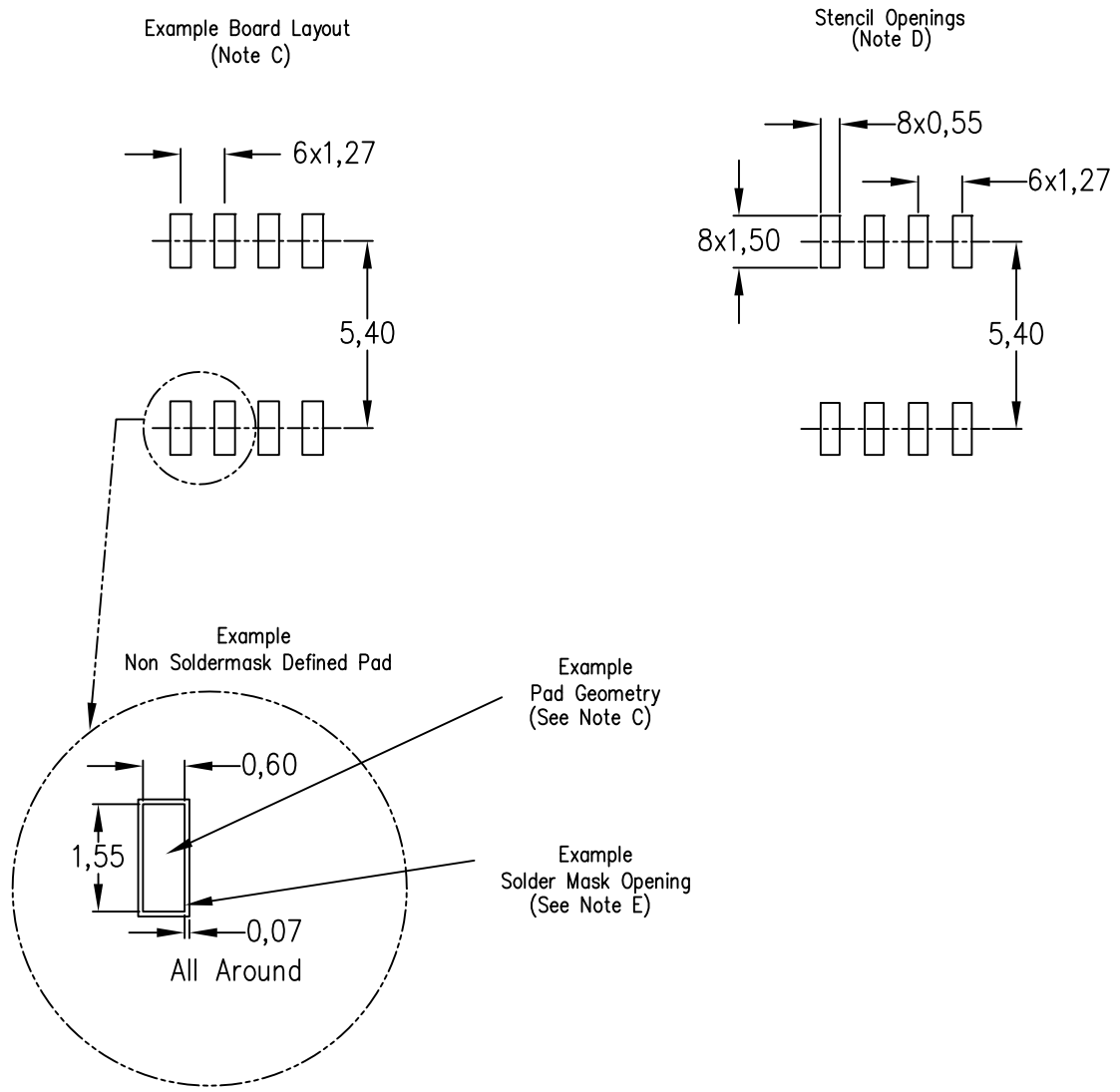
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7420DR	SOIC	D	8	2500	367.0	367.0	35.0
ISO7420MDR	SOIC	D	8	2500	367.0	367.0	35.0
ISO7421DR	SOIC	D	8	2500	367.0	367.0	35.0

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AA.

D (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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